

MEDIUM POWER LINEAR AMPI

Typical Applications

- PCS Communication Systems
- 2.5 GHz ISM Band Applications
- Wireless LANs

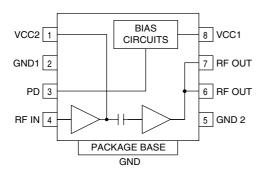
- Commercial and Consumer Systems
- Portable Battery Powered Equipment

Product Description

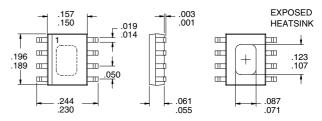
The RF2128P is a medium-power, high-efficiency, linear amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 2.45 GHz ISM applications such as WLAN and POS terminals. The part also will function as the final stage in digital PCS phone transmitters requiring linear amplification operating between 1900 MHz 2200 MHz, with over 100 mW transmitted power, or as the driver stage for the RF2125 high power amplifier. A simple power down function is included for TDD operation. The part is packaged in a low-cost plastic package with a metal backside.

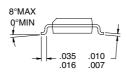
Optimum Technology Matching® Applied

Si BJT **√** GaAs HBT GaAs MESFET Si Bi-CMOS SiGe HBT Si CMOS



Functional Block Diagram





Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.

Package Style: PSOP-8

Features

- Single 3.0V to 6.5V Supply
- 100mW Linear Output Power
- 28dB Small Signal Gain
- 33% Efficiency
- Digitally Controlled Power Down Mode
- 1900MHz to 2500MHz Operation

Ordering Information

RF2128P Medium Power Linear Amplifier RF2128P PCBA Fully Assembled Evaluation Board

RF Micro Devices. Inc. 7625 Thorndike Road Greensboro, NC 27409, USA

Tel (336) 664 1233 Fax (336) 664 0454 http://www.rfmd.com

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RF2128P

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (V _{CC})	-0.5 to +7.5	V_{DC}
Power Down Voltage (V _{PD})	-0.5 to +5.5	V
DC Supply Current	125	mA
Input RF Power	+12	dBm
Output Load	20:1	
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.



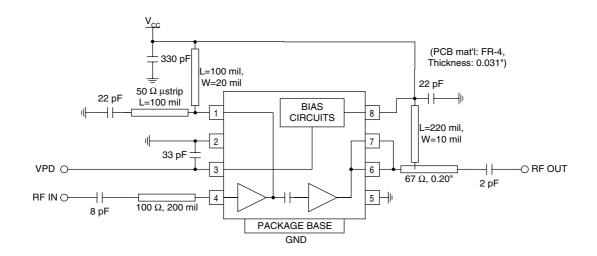
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Parameter	Specification		Unit	Condition		
Parameter	Min.	Тур.	Max.	Offic	Condition	
Overall					T=25 °C, V _{CC} =5 V, V _{PD} =5.0 V,	
					Freq=2400MHz	
Frequency Range		1900 to 2500		MHz		
Maximum Output Power		+22		dBm	V_{CC} =5.0 V, V_{PD} =5.0 V, P_{IN} =-3.0 dBm	
		>+24		dBm	V_{CC} =6.0 V, V_{PD} =5.5 V, P_{IN} =0 dBm	
1dB Compression Output Power		+21		dBm		
Total CW Efficiency		33		%	Maximum output	
Small-signal Gain		28		dB		
Second Harmonic		-23		dBc		
Third Harmonic		-19		dBc		
Isolation		15		dB	$V_{PC}=0.2V$	
Input VSWR		2:1				
Input Impedance		50		Ω		
Noise Figure		7		dB		
Two-tone Specification						
Average Two-Tone Power		+17		dBm	PEP-3dB	
IM ₃		-27		dBc	P _{OUT} =+14dBm for each tone	
IM ₅		-40		dBc	P _{OUT} =+14dBm for each tone	
IM7		-44		dBc	P _{OUT} =+14dBm for each tone	
Two-Tone Power-Added Efficiency		30		%		
Power Down Control						
Power Down "ON"		V _{CC}		V	Voltage supplied to the input; device is "on"	
Power Down "OFF"	0		1.2	V	Voltage supplied to the input; device is "off"	
Power Supply						
Voltage		5		V	Specifications	
		3.0 to 6.5		V	Operating	
Current		50	65	mA	Operating Idle	
		85		mA	At maximum output power	
Current			10	μΑ	Power Down	

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Pin	Function	Description	Interface Schematic
1	VCC2	Power supply for the driver stage and interstage matching. External matching on this pin is required to optimize the gain. The matching on this port also greatly affects the input impedance. A decoupling capacitor of 330pF is required, together with a series RC for tuning for maximum gain at the desired frequency. See the application information for details.	
2	GND1	Ground connection for the driver stage. Keep traces physically short and connect immediately to the ground plane for best performance.	
3	PD	Power Down control. When this pin is "low", all circuits are shut off. A "low" is typical 1.2 V or less at room temperature. When this pin is "high", all circuits are operating normally. A "high" is V_{CC} . If PD is below V_{CC} output power and performance will be degraded. This could be used to obtain some gain control, but results are not guaranteed.	
4	RF IN	RF Input. This is a 50Ω input, but the actual impedance depends on the matching provided on pin 1. An external DC blocking capacitor is required if this port is connected to a DC path to ground.	
5	GND2	Ground connection for the output stage. Keep traces physically short and connect immediately to the ground plane for best performance.	
6	RF OUT	RF Output and power supply for the output stage. Bias for the output stage needs to be provided on this pin. This can be done through a quarter-wave microstrip that is RF grounded on the other end. For matching to 50Ω , an external series microstrip line is required.	
7	RF OUT	Same as pin 6.	
8	VCC1	Power supply for the bias circuits. An external RF bypass capacitor of 22 pF is required. Keep the traces to the capacitor as short as possible, and connect the capacitor immediately to the ground plane.	
Pkg Base	GND	Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., vias under the device may be required.	

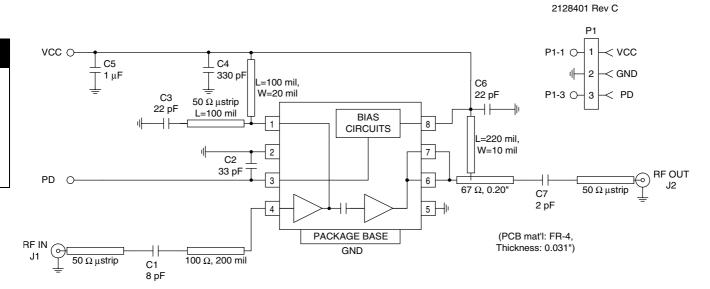
Application Schematic 2450MHz Operation



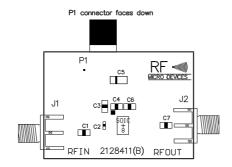
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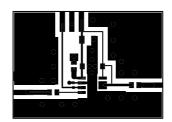
Evaluation Board Schematic 2450 MHz Operation

(Download Bill of Materials from www.rfmd.com.)



Evaluation Board Layout 1.572" X 1.121"





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